

**VSP-MIKRON** $V_{RRM}=1700V$ $I_F = 50A$ **Diode-Die****KD50170F**

Die Size-7.54 x 7.54mm.

Ultra low losses

Passivation : Silicon Oxide

Maximum rated values

Preliminary

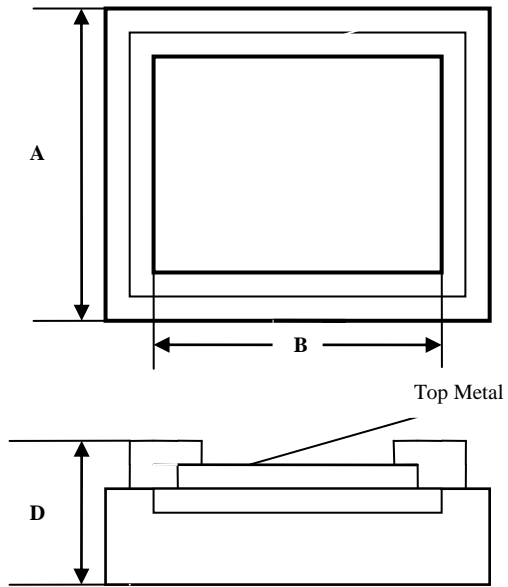
Parameter	Symbol	Unit	min	max
Repetitive peak reverse voltage	V_{RRM}	V	-	1700
Continuous forward current	I_F	A	-	50
Repetitive peak forward current*	I_{FRM}	A	-	100
Junction temperature	T_{vj}	°C	-	150

*Limited by $T_{vj\ max}$ **Diode Characteristics values**

Parameter	Symbol	Conditions	min	typ	max	Unit
Continuous forward voltage	V_F	$I_F=50A, T_{vj}= 25^\circ C$		2.4		V
Continuous reverse current	I_R	$V_R=1700V \begin{matrix} T_{vj}= 25^\circ C \\ T_{vj}= 125^\circ C \end{matrix}$		2.0	100	μA mA
Peak reverse recovery current	I_{RRM}	$I_F=50A, V_R=700V,$ $di_F/dt=200A/\mu S,$ $T_{vj}= 25^\circ C$		tbd		A
Recovered charge	Q_{rr}			tbd		μC
Reverse Recovery Time	t_{rr}			tbd		nS
Reverse Recovery Time	t_{rr}	$I_F=1A, V_R=30V,$ $di_F/dt=200A/\mu S.$		100	120	nS

Mechanical properties*Top metal: **Al-Ti** – for Wire Bonding.**Backside metal: **Ti-Ni-Ag** – for Soldering.*

DIM	ITEM	μm
A_x A_y	Die Size	7540 7540
D	Thickness	460max.
Scribe line Width		60



www.vsp-mikron.com